

Please amend the paragraph beginning at page 12, line 17, as follows:

The Cu films 46 and 50 are covered by the top dielectric film 54 made of $[\text{SiO}_2]$ SiON except for the electrode pads 48 which are exposed by openings 56 formed in the top dielectric film 54 and the polyimide overcoat film 58. The polyimide film 58 has also openings 59 therein for exposing portions of the top dielectric film 54 overlying the fuse elements 52.

IN THE CLAIMS:

Please cancel claims 1-5 and 12-14 without prejudice or disclaimer of the subject matter thereof.

1. – 5.(Cancelled)

6.(Original)A semiconductor device comprising a substrate, a first dielectric film overlying said substrate, a pair of fuse terminals embedded in a surface portion of said first dielectric film, a fuse element formed on said first dielectric film and connected to said pair of fuse terminals.

7.(Original)The semiconductor device as defined in claim 6, further comprising a plurality of top interconnect lines each having a line body formed as a common layer with said fuse terminals and a protective film formed on said line body as a common layer with said fuse element.

8.(Original)The semiconductor device as defined in claim 6, further comprising a plurality of electrode pads each having a pad body formed as a common layer with said fuse terminals and a protective film formed on said pad body as a common layer with said fuse element.

9.(Original)The semiconductor device as defined in claim 7, further comprising a second dielectric film formed on said first dielectric film and having a plurality of openings each exposing one of said electrode pads.

10.(Original)The semiconductor device as defined in claim 9, wherein said fuse element is made of TiN film, stacked films including TiN film and a Ti film or a TiW film.

11.(Original)The semiconductor device as defined in claim 9, wherein said fuse terminals are made of Al, Al alloy, Cu or Cu alloy.

12. – 14.(Cancelled)